## 強誘電 HfO2の分極繰り返しに伴う劣化に対する電荷注入の効果に関する考察 Consideration of Charge Injection Effect on the Degradation of Ferroelectric HfO2 during Bipolar Voltage Cycling

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**[Introduction]** It is commonly observed that the switchable polarization ( $P_{sw}$ ) of ferroelectric (FE) HfO<sub>2</sub> degraded during bipolar voltage cycling, which can be a major issue that leads to the instability of the device operations. Despite the well know fabrication process of FE-HfO<sub>2</sub>, the mechanism for the fatigue effect, whether it is due to atomic re-orientation or the increase in defect density, is still remains unclarified. Hence, in this study, we investigate the possible factors contributing to the degradation of FE-HfO<sub>2</sub> during dipolar voltage cycling.

**[Experimental]** Two types of MFM capacitors with ~30 nm-thick of HfO<sub>2</sub> were fabricated: 1.5 cat% Y-doped HfO<sub>2</sub> (Y-HfO<sub>2</sub>) and pure HfO<sub>2</sub>. Both samples were fabricated by sputtering HfO<sub>2</sub> on heavily doped Ge substrates, where the Y-dopant was introduced by co-sputtering HfO<sub>2</sub> and Y<sub>2</sub>O<sub>3</sub>. Then, the stacks were annealed at 600°C in N<sub>2</sub> ambient for 30 s, followed by the deposition of Au top electrodes. The degradation of FE-properties was characterized by 12 V bipolar voltage cycling at the frequency of 10 kHz and constant DC-bias stress.

**[Results and Discussions]** Figure 1 shows the P-V hysteresis of Y-HfO<sub>2</sub> at a different number of cycles during the bipolar cycling. The change in  $P_{sw}$  during cycling is summarized in Fig. 2. There was a noticeable increase in the  $P_{sw}$  at the beginning of the cycling. After 10<sup>3</sup> cycles,  $P_{sw}$  gradually decreased, and rapidly dropped after 10<sup>4</sup> cycles. From the P-V hysteresis, the dielectric constant of HfO<sub>2</sub> ( $\varepsilon_{HfO2}$ ) can be roughly estimated from the slop (dP/dV) as indicated in Fig.1. By assuming that there was no reaction at HfO<sub>2</sub>/Ge interface during voltage cycling, the  $\varepsilon_{HfO2}$  decreased constantly with the number of voltage cycling, as shown in Fig. 2 This could suggest a phase transformation during the voltage cycling, regarding that the ferroelectricity of HfO<sub>2</sub> originates from the *o*-phase, and the  $\varepsilon_{HfO2}$  is strongly dependent on its crystal phases [1]. To evaluate the dominant factors that determine the degradation mechanism, DC-bias stress of +9 V and +12 V were applied on Y-HfO<sub>2</sub> before making P-V measurement. The injected charges ( $Q_{inj}$ ) were calculated and are plotted as the horizontal axis of Fig.3 At a certain amount of  $Q_{inj}$ , both the P<sub>sw</sub> of Y-HfO<sub>2</sub> and pure-HfO<sub>2</sub> (data not shown) stressed at 9 V and 12 V began to drop. Also, the  $\varepsilon_{HfO2}$  was also estimated after the DC-bias stress (shown in Fig. 3). Both the estimated  $\varepsilon_{HfO2}$  during the voltage cycling and after DC-bias stress monotonically in a similar trend along with the reduction in P<sub>sw</sub>. Thus, it is reasonable to consider that  $Q_{inj}$  is one of the crucial factors that determine the degradation voltage cycling. **References:** [1] K. Kita, *et.al.*, APL. **86**, 102906 (2005)



**Fig1.** The P-V hysteresis of Y-HfO<sub>2</sub> at its pristine,  $10^3$ , and  $10^5$  cycles. The  $\varepsilon_{\text{HfO2}}$  was estimated from the slope of the fitting above the coercive field.

**Fig.2** The change in  $P_{sw}$  (right) and  $\varepsilon_{HfO2}$  (left) during bipolar voltage cycling at 12 V and 10 kHz.

**Fig.3** The change in  $P_{sw}$  (right) and  $\varepsilon_{HfO2}$  (left) after stressed at 9 V and 12 V for a certain time. The  $Q_{inj}$  were calculated and are shown above.